TOSHIBA DIODE SILICON EPITAXIAL PLANAR TYPE

155201

ULTRA HIGH SPEED SWITCHING APPLICATION.

Low Forward Voltage $: V_{F(3)} = 0.9V \text{ (Typ.)}$

Fast Reverse Recovery Time: trr=1.6ns (Typ.)

Small Total Capacitance $: C_T = 0.9pF (Typ.)$

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT	
Maximum (Peak) Reverse Voltage	v_{RM}	85	V	
Reverse Voltage	v_{R}	80	V	
Maximum (Peak) Forward Current	$I_{ extbf{FM}}$	300 (*)	mA	
Average Forward Current	IO	100 (*)	mA	
Surge Current (10ms)	I_{FSM}	2 (*)	Α	
Power Dissipation	P	200	mW	
Junction Temperature	$T_{ m j}$	125	°C	
Storage Temperature Range	T _{stg} -55~125		°C	

Unit in mm 0.55MAX ANODE 1 2. CATHODE 1, 2 3. ANODE 2 **JEDEC EIAJ** TOSHIBA 1-4E2A

Weight: 0.13g

(*) Unit Rating. Total Rating=Unit Rating×1.5.

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

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CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT		
Forward Voltage	V _{F(1)}	I _F =1mA	_	0.60	_	V		
	$V_{F(2)}$	$I_{\mathbf{F}} = 10 \text{mA}$	_	0.72	_			
	$v_{F(3)}$	$I_{ m F}\!=\!100{ m mA}$		0.90	1.20			
Reverse Current $ \frac{I_{R(1)}}{I_{R(2)}} $	I _{R (1)}	$V_R = 30V$	_	_	0.1	μ A		
	$I_{R(2)}$	$V_R = 80V$	_	_	0.5			
Total Capacitance	C_{T}	$V_R=0$, f=1MHz	_	0.9	3.0	pF		
Reverse Recovery Time	t_{rr}	I _F =10mA (Fig.1)	_	1.6	4.0	ns		

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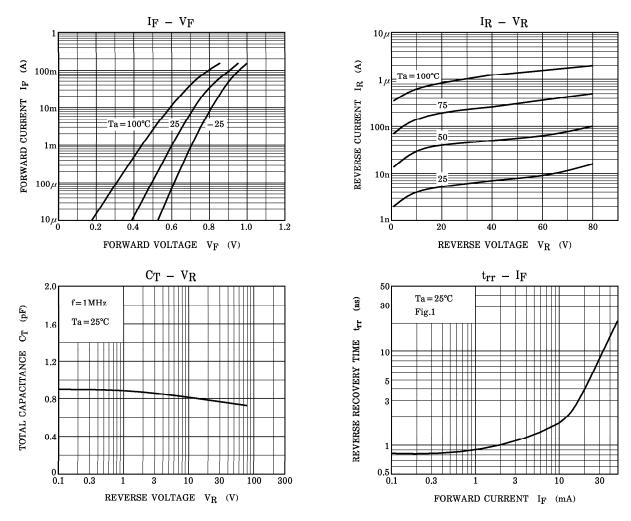


Fig.1 Reverse recovery time (t_{rr}) test circuit

